



Sheet 1 of 6

Form 1449*	Atty. Docket No.: 303.672US1	Serial No. 09/483,881
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Kie Y. Ahn et al.	
	Filing Date: January 18, 2000	Group: Unknown

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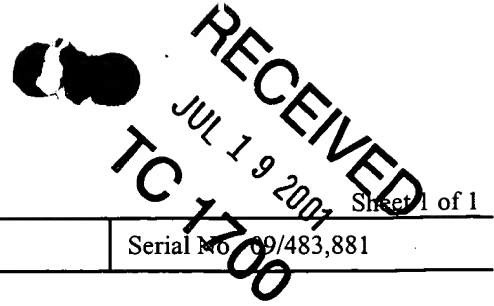
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Group: 1752

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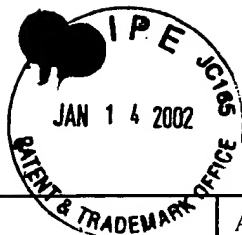
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